



Advanced Single-Channel High-Voltage Isolated Automotive Gate Driver for SiC MOSFETs/IGBTs

GD3160

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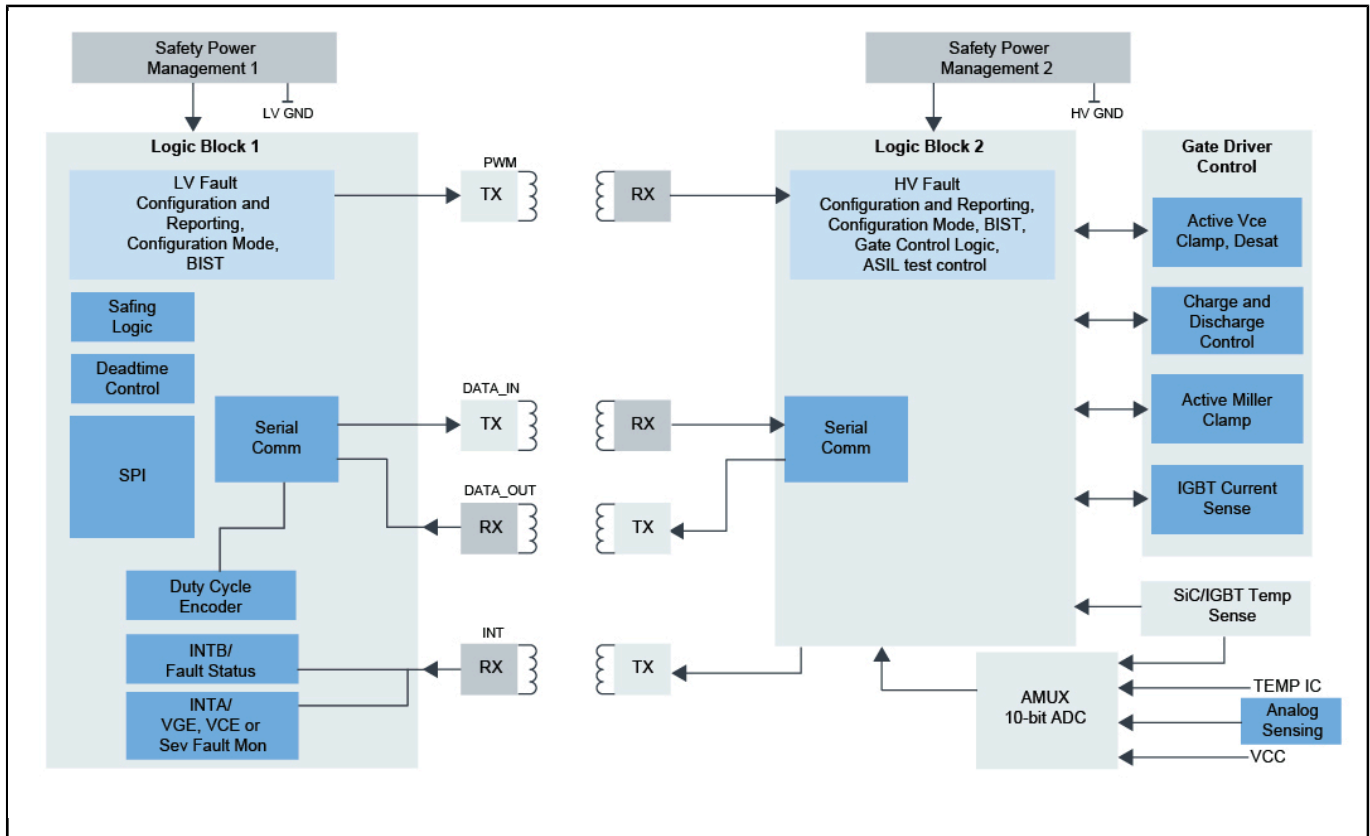
The GD3160 is an improved, advanced single-channel high-voltage isolated gate driver with enhanced features for driving and protecting silicon carbide (SiC) MOSFETs and functional safety.

The GD3160's SPI programmable drive, protection and fault reporting features allow users to optimize conditions for driving and protecting almost any SiC MOSFET or Si IGBT power switch.

ISO 26262 compliant and automotive qualified, the GD3160 integrates BOM saving and functional safety features to support implementing ASIL D compliant and power density efficient xEV inverter solutions.

GD3160 silicon and enablement (documentation, software and boards) are available for selected customers (NDA required). Please contact your local NXP sales representative for more information.

GD3160 Block Diagram Block Diagram



View additional information for [Advanced Single-Channel High-Voltage Isolated Automotive Gate Driver for SiC MOSFETs/ IGBTs](#).

Note: The information on this document is subject to change without notice.

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